

Substitute for Form 1449 A & B/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet	of	Attorney Docket Number	960045E
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
		US			

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			
LTUE	1	JP	3-64964		03-20-1991	Toshiba Corp.	Abstract
LTUE	2	JP	3-174765		07-29-1991	OKI Electric Ind. Co. Ltd.	Abstract
LTUE	3	JP	3-174766		07-29-1991	Toshiba Corp.	Abstract
LTUE	4	JP	5-136369		06-01-1993	Sharp Corp.	Abstract
LTUE	5	JP	5-145036		06-11-1993	Toshiba Corp.	Abstract
LTUE	6	JP	5-218332		08-27-1993	Samsung Electron Co. Ltd.	Abstract
LTUE	7	JP	5-243517		09-21-1993	NEC Corp.	Abstract
LTUE	8	JP	5-304269		11-16-1993	NEC Corp.	Abstract
LTUE	9	JP	6-37272		02-10-1994	Toshiba Corp.	Abstract
LTUE	10	JP	6-37273		02-10-1994	Toshiba Corp.	Abstract
LTUE	11	JP	6-37280		02-10-1994	Toshiba Corp.	Abstract
LTUE	12	JP	6-120447		04-28-1994	Mitsubishi Electric Corp.	Abstract

NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.				Translation ⁶

Examiner Signature	/Lynette Umez Eronini/ (07/06/2006)	Date Considered
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or in the comment box of this document. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to indicate here if English language Translation is attached.

INFORMATION	Atty. Docket No. 960045E	Serial No. To be assigned
DISCLOSURE	Applicant(s): Taiji EMA et al.	
CITATION	Filing Date: Herewith	Group Art Unit: To be assigned

PTO-1449

U.S. PATENT DOCUMENTS

Examiner		Document No.	Name	Date	Class	Subclass	Filing Date
Initial							(If appropriate)
LTUE	AB	5,502,336	Park et al.	03/96			
LTUE	AC	5,479,054	Tottori	12/95			
LTUE	AD	5,338,700	Dennison et al.	08/94			
LTUE	AE	4,974,040	Taguchi et al.	11/90			
LTUE	AF	5,150,278	Gonzalez et al.	09/92			
LTUE	AG	5,196,910	Moriuchi et al.	03/93			
LTUE	AH	5,605,857	Jost et al.	02/97			
LTUE	AI	5,324,681	Lowrey et al.	06/94			
LTUE	AJ	5,292,677	Dennison	03/94			
LTUE	AK	5,281,549	Fazan et al.	01/94			
	AL						
	AM						

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		Document No.	Date	Country	Translation
(Yes or No)					
LTUE	AN	61-176148	08/07/96	Japan	
LTUE	AO	3-167874	07/19/91	Japan	
LTUE	AP	5-218332	08/27/93	Japan	
	AQ				

OTHER DOCUMENTS

<u>LTUE</u>	AR	B.LUTHER et al.; Planar Copper-Polyimide Back End of the Line"; Proceedings of 10 th International VMIC; pages 15-21; June 1993.
<u>LTUE</u>	AS	B.M. SOMERO et al.; "A Modular in-situ Integration Scheme for Deep Submicron", Proceedings of 10 th International VMIC; pages 28-34; June 1993.
<u>LTUE</u>	AT	M.F. CHISHOLM et al.; "A High Performance 0.5 um Five-Level Metal Process with Extendibility of Sub-Half Micron"; pages 22-28; June 1994.
<u>LTUE</u>	AU	M. RUTTEN et al.; "Pattern Density Effects in Tungsten CMP", Proceedings of 12 th International VMIC; pages 491-497; June 1995.
<u>LTUE</u>	AV	I. NAIKI et al.; "Center Wordline Cell: A New Symmetric Layout Cell for 64Mb SRAM"; Technical Digest of IEDM; pages 817-820; December 1993.
<u>LTUE</u>	A W	T. KAGA et al.; "A 0.29-um ² MIM-Crown Cell and Process Technologies for 1-Gigabit DRAMs"; Technical Digest of IEDM; pages 927-929; December 1994.
<u>LTUE</u>	AX	H.K. KANG et al.; "Highly Manufacturable Process Technology for Reliable 256 Mbit and 1 Gbit DRAMs"; Technical Digest of IEDM; pages 635-638; December 1994.
<u>LTUE</u>	A Y	Y. OHJI et al.; "Ta ₂ O ₅ Capacitors Dielectric Material for Giga-bit DRAMs"; Technical Digest of IEDM; pages 111-114; December 1995.
<u>LTUE</u>	AZ	Y. NISHIOKA et al.; "Giga-bit Scale DRAM Cell with New Simple Ru/(Ba,Sr)TiO ₃ /Ru Stacked Capacitors Using X-ray Lithography"; Technical Digest of IEDM; pages 903-906; December 1995.
<u>LTUE</u>	BA	K.P. LEE et al.; "A Preocess Technology for 1 Giga-bit DRAM"; Technical Digest of IEDM; pages 907-910; December 1995.
<u>LTUE</u>	BB	J.K. PARK et al.; "Isolation Merged Bit Line Cell(IMBC) for 1Gb DRAM and Beyond". Technical Digest of IEDM; pages 911-914; December 1995.
<u>LTUE</u>	BC	
<u>LTUE</u>	BD	

Examiner

Date Considered
/Lynette Umez Eronini/ (07/06/2006)